Temperature dependence of carbon nanofiber resistance
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Abstract. Transport properties under current stress are examined for a carbon nanofiber (CNF) on an insulating substrate between tungsten-deposited gold electrodes. The temperature dependence of CNF resistance is determined based on our previously reported heat transport model. The measured devices exhibit thermal activation behavior, suggesting transport in a disordered medium. The extracted activation energies fall within the 22–35 meV range.

PACS: 72.80.Ng Disordered solids, 72.80.Vp Electronic transport in graphene, 73.63.Fg Nanotubes.
Key Words: Carbon nanofiber (CNF), heat transport model, thermal activation, disordered media

INTRODUCTION
Carbon nanofibers (CNFs) belong to the family of covalent nanocarbon materials and are promising candidates for next-generation on-chip interconnect materials [1]-[6]. CNFs are immune to electromigration, resulting in much higher current capacity than Cu [7]-[8], and are easily obtainable with aligned vertical growth at moderately low temperatures, which are suited for on-chip via interconnect applications [4]. Transport properties of this material at elevated temperatures are of scientific and technological interest. While it is possible to perform electrical measurements on CNFs at elevated temperatures, various transport mechanisms within the test structure needs to be differentiated. It is nontrivial to study a single CNF since it has an extremely small heat capacity and maintaining thermal equilibrium is highly challenging. One way to overcome this problem is to embed a parallel array of CNFs in an insulator inside a via hole so that the system heat capacity will be effectively increased [9]. Using this approach, thermally activated transport, typical of transport in disordered media [10], was observed [9]. In this work, we raise the temperature of a single CNF using Joule heating, which is placed horizontally on metal electrodes on an insulating substrate. Current is progressively applied and the total resistance of a CNF between two electrodes is measured after and during each current stress cycle, until breakdown occurs. Total resistance does not change if the measurement is performed after completion of a stress cycle (with the CNF cooled down to ambient temperature). But the average resistance obtained during each cycle decreases with increasing stress current from one cycle to the next (with the CNF subject to increasing Joule heating). We convert stress current to CNF average temperature using our previously reported heat transport model [11], and obtain conductivity as a function of temperature.

CURRENT STRESS EXPERIMENT
A multi-wall carbon nanotube (CNT) consists of parallel rolled graphene sheets with a diameter ranging from several nm to several 100 nm. Thus as in single-wall CNT, the interior is hollow. A carbon nanofiber (CNF) also has parallel rolled graphene sheets as the outer layers, but has a stacked-cup structure in the interior which is no longer hollow. Adjacent cups are separated by ~ 0.5 nm, thus electron transport occurs largely along the outer graphene layers. A transmission electron micrograph (TEM) image of a CNF is shown in figure 1. In CNTs, if the structure is free of defects and impurities, transport is ballistic in low fields with conductance equal to a multiple of quantum conductance \( G_0 = q^2/h \) (\( q \) is the unit electronic charge and \( h \) the Planck constant), but classical (ohmic) in high fields [12], since electrons can gain sufficiently high kinetic energy in high fields and emit phonons (inelastic scattering) [13]. Our
CNFs are metallic [14], but contain impurities and/or lattice defects in the outer graphene layers and in the stacked-cup layers, giving rise to electron traps [9]. As far as electrical transport properties are concerned, typical metals are rather immune to impurities/defects due to their extremely large electron density of states at the Fermi level, but CNFs or CNTs approach a semi-metal 2D graphene in the large diameter limit, and their counterpart is much smaller than that in typical metals [15], resulting in vulnerability to disorder. In our CNFs, transport is largely dictated by disorder [10]. CNFs used in these measurements were grown using plasma-enhanced chemical vapor deposition method with Ni catalyst [12]. The diameters of these CNFs range from 90 nm to 156 nm. Using focused ion beam, tungsten (W) was deposited onto the CNF at pre-fabricated gold (Au) electrode contacts [8]. Figure 2 inset shows a scanning electron microscope (SEM) image of such a CNF with W-Au electrodes. All the measurements are performed in ambient. Total resistance is in the kΩ range. The current-voltage ($I$-$V$) behavior is linear and the electrode contacts are robust after W deposition, minimizing the unwanted contact effects [8]. From four-point probe measurements, the average resistivity for unstressed CNF is determined to be $\rho_{\text{CNF}} = 1.3 \times 10^{-5} \, \Omega \text{m}$ [17]. Using a typical diameter $d \sim 100$ nm and length $L \sim 4$ μm, we obtain a CNF resistance $R_{\text{CNF}} = \rho_{\text{CNF}} \times L / \pi (d/2)^2 = 6.4$ kΩ at 300 K. The total resistance in figure 2 is in this range, indicating that contact resistance $R_c$ satisfies $R_c < R_{\text{CNF}}$ (or $R_c \ll R_{\text{CNF}}$) consistently, and thus it is reasonable to neglect $R_c$ in our analysis.

**Figure 1.** TEM image of a CNF using plasma-enhanced chemical vapor deposition method with Ni catalyst.

Stress current is applied progressively, i.e., in the first cycle, a small constant current is applied for three minutes, and in the second cycle, a larger constant current is applied for another three minutes, etc. When resistance is measured after each stress cycle using much smaller current and voltage, the CNF is cooled down to ambient temperature. Total resistance measured between the two electrodes changes very little, by at most 20% after multiple stress cycles [8]. This behavior is in sharp contrast with results for current stressing of CNF drop-casted on Au electrodes, where the total resistance drops by orders of magnitude until breakdown, largely due to contact resistance reduction [8]. This suggests that for CNF between W-Au electrodes, the contact resistance is not only unaffected by current stressing, but also small relative to CNF resistance. When the average resistance is measured during each stress cycle, it decreases from one cycle to the next. Figure 2 shows the total resistance as a function of stress current for four
different devices, averaged over each stress cycle. Since the device is subject to Joule heating during current stress, and since its average temperature must increase with increasing stress current, the total resistance must then decrease with elevated temperature. The stress current versus temperature behavior is examined in the following section.

Figure 2. Total resistance $R$ as a function of stress current $I_s$, averaged over each stress cycle for four devices (filled circle, open circle, triangle, and square). $I_s = 0$ corresponds to the ambient temperature data. Inset: SEM image of CNF device. Supported segments are indicated by solid lines and suspended segments by broken lines.

CONVERSION OF STRESS CURRENT TO AVERAGE TEMPERATURE

Our one-dimensional heat transport model [12] takes into account Joule heat generation by stress current, dissipation to SiO$_2$ substrate/electrode, and diffusion, as given by

$$d^2 \Delta T(x)/dx^2 - a(x)^2 \Delta T(x) = -b J^2.$$  

(1)

$\Delta T(x) = T(x) - T_0$, where $T_0$ is ambient temperature. $J$ is the current density and $b = 1/(\kappa \sigma)$, where $\kappa$ is the thermal conductivity and $\sigma$ is the electrical conductivity of the CNF. $a(x)$ is a dissipation factor modeled by a piecewise function. $a_i$ is for the suspended segment, $a_s$ is for the SiO$_2$ substrate supported segment, and $a_e$ is for the W-Au electrode. $a_i < a_s < a_e$ is expected. The analytical solution of $\Delta T(x)$ is connected at the junction with different $a$'s, by demanding continuous $\Delta T$ and $d\Delta T/dx$ [11]. Suspended/supported segments are identified by analyzing SEM image contrast [11]. In figure 3(a), the device has suspended 1 (bright), supported (dark) and suspended 2 (bright) segments. Breakdown occurred in suspended 1 segment, where the highest temperature $T_{\text{max}}$ just exceeded the threshold temperature $T_{\text{th}}$. Thus, we consider only suspended 1 and supported segments for average temperature determination.

Setting $a_i \sim 0$ and $a_e \sim \infty$ in our model, we fit the only unknown parameter $a_s$ to recover $T_{\text{max}} = T_{\text{th}}$ at measured $J_{\text{max}}$. Hata et al. reported that the weight reduction for a single-walled carbon nanotube forest (film) occurred in the 550-750 ºC range in the thermo-gravimetric measurement [19]. We choose $T_{\text{th}} = 900$ K, which is close to the onset of breakdown as in our previous analysis [7], [11]. For the CNF in figure 3(a), $a_s$ is found 3.6 $\mu$m$^{-1}$ and $T(x)$ at $J_{\text{max}}$ is calculated and shown in figure 3(b). $T(x)$ is parabolic in the suspended segment due to minimal heat dissipation, while $T(x)$ is constant in the supported segment due to negligible diffusion. The $T_{\text{max}}$ location compares well with the measurement. Since $\Delta T(x) \propto J^2$ as shown in Eq. (1), spatially averaged temperature $\Delta T_{\text{av}}(J)$ is given by $\Delta T_{\text{av}}(J_{\text{max}}) J^2/J_{\text{max}}^2$. This is how we relate stress current to average temperature.

The stress current in figure 2 is now converted to temperature. We assume that the CNF contribution to
total resistance is dominant in the W-Au electrode as suggested earlier, and evaluate CNF conductivity \( \sigma_{\text{CNF}} \) using the Ohm's law with the length and cross-section area. In figure 4, an Arrhenius plot of \( \sigma_{\text{CNF}} \) versus \( 1/T_{\text{av}} \) is shown for the four devices. This behavior is analyzed using the relation

\[
\sigma_{\text{CNF}} = \sigma_0 \exp(-E_a/k_B T),
\]

where \( k_B \) is the Boltzmann constant, \( \sigma_0 \) is a device-dependent parameter, and \( E_a \) is the activation energy. From Eq. (2), \( E_a \) is estimated to range from 22 to 35 meV.

![Figure 3](image)

**Figure 3.** (a) SEM image of the same device shown in figure 2(a) after breakdown. Supported segments are indicated by solid lines and suspended segments by broken lines. (b) Calculated temperature profile \( T(x) \).

The behavior of \( \sigma_{\text{CNF}}(1/T) \) in figure 4 appears for carrier transport in disordered media, which is in sharp contrast to the usual behavior of metals showing lower conductivity at higher temperature [10]. Our CNFs are metallic [17], but contain impurities and/or lattice defects in the outer graphene layers, giving rise to electron traps [9] due to the small Fermi density of states. Joule heating serves to de-trap trapped electrons through thermal activation, creating additional carriers. This assertion is supported by the Arrhenius behavior for all four devices shown in figure 4. Accordingly, more electrons participate in transport as the CNF temperature increases, resulting in decrease in resistance. Since resistance at ambient temperature is unaffected before and after current stress, electrons must be recaptured by traps as the temperature returns to ambient. Thus this trapping/de-trapping process is completely reversible. Figure 4 reveals a significant variation in \( \sigma_0 \) (vertical axis intercept) but similar activation energies \( E_a \) (slopes). Since CNFs were synthesized using the same growth conditions, defects themselves should be the same (sharing similar \( E_a \)'s). However, their density could be different from device to device because of the large CNF diameters, ranging from 90 nm to 156 nm, which explains the significant variation in \( \sigma_0 \).

Graphite’s in-plane conductivity ranges between 330 and 2000 S/cm at 300 K [20]. Our measured CNF conductivity at 300 K given in figure 4 ranges from 200 to 900 S/cm, consistent with transport in a disordered medium. In our previous work [21], we reported that breakdown occurs along the stacked-cone surface, originating from void formation and growth as a result of Joule heating. If the temperature is elevated but stays below the threshold temperature, it is expected that the morphology change, if any, is reversible, because the total resistance comes back to its original value.

**COMPARISON TO PREVIOUS STUDY**

In our previous study [16], we examined transport in vertically aligned CNF arrays in a via interconnect...
structure. The CNF arrays were grown on a Ti underlayer as the as-grown electrode, with a Ti/Pt contact pad deposited on top after oxide encapsulation. I-V measurement was performed in the temperature range from 4.2 to 350 K. The entire structure was subject to heating/cooling while the temperature was measured. The measured conductivity was fitted to \( \sigma_{\text{CNF}} = \sigma_0 \exp(-E_a/k_B T) + \sigma_1 \). The term \( \sigma_1 \) accounted for the finite residual contribution in the limit of \( T \to 0 \), and \( \sigma_{\text{CNF}} \) was shown to reduce to Eq. (2) at or above ambient temperature. Using this fitting equation, the activation energy \( E_a \) was extracted to be 26 meV [9]. The present activation energy range of 22~35 meV is consistent with this value. Despite the obvious differences in device structure, temperature range, and temperature determination, the similarity in \( E_a \) is remarkable but expected as both systems share the same thermal activation process. Since defects or impurities are unavoidable in CNFs with diameters \( \sim 100 \) nm, it is meaningful to elucidate the CNF transport properties at elevated temperatures and in high fields (high current densities), in assessing its potential in interconnect as well as other applications. The reversible temperature-dependent transport in CNFs may also be suitable for thermistor applications.

As discussed in [3], carbon nanotubes (CNTs) show the opposite trend, i.e., the conductivity decreases with temperature, because phonon scattering dominates at higher temperature and the influence of impurities/defects is not significant. In growing a very narrow CNT, impurities/defects are much less likely to be present than in a much wider CNF. Some of such defects are visible in the TEM image shown in figure 1. Our observation is consistent with the expectation that phonon-limited transport occurs in CNTs and disorder-limited transport in CNFs due to the presence of large numbers of defects.

As long as breakdown does not occur, the change in resistance with temperature is reversible. In our previous work [21], we reported that breakdown occurs along the stacked-cone surface, originating from void formation and growth as a result of Joule heating. If the temperature is elevated but stays below the breakdown threshold, it is expected that the morphology change, if any, is reversible, since the total resistance returns to its ambient value upon cooling.

Tsuzuku and Saito [22] showed that the activation energy for thermal depinning of dislocations in graphite ranges between 40 meV and 30 meV before and after bromination, respectively, and 6 meV for the boronateds. Our estimated activation energies in the 22~35 meV range are consistent with these values and point to similar defect origins in graphitic materials. The reversible and temperature-dependent conductivity may lead to potential application as a thermistor. Also, such behavior is critical in thermal management considerations during the design process for using CNFs as on-chip interconnects.

![Figure 4. Conductivity \( \sigma_{\text{CNF}} \) as a function of inverse average temperature \( 1/T_{av} \) for the same four devices (the same symbols assigned) as in figure 2(b).](image-url)
CONCLUSION

Transport properties of a horizontally placed CNF connected between W-Au electrodes, one of the simplest test structures for interconnect applications, are studied. The temperature dependence of CNF resistance is determined based on our previously developed heat transport model [11]. CNF resistance decreases with increasing temperature, and the CNF conductivity has an Arrhenius behavior, with extracted activation in the 22–35 meV range, consistent with 26 meV we extracted previously using a vertical via structure [9]. This work was supported by the United States Army Space and Missile Defense Command (SMDC) and carries Distribution Statement A, approved for public release, distribution unlimited.
REFERENCES


**Figure Captions**

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**Figure 3.** (a) SEM image of the same device shown in figure 2(a) after breakdown. Supported segments are indicated by solid lines and suspended segments by broken lines. (b) Calculated temperature profile $T(x)$.

**Figure 4.** Conductivity $\sigma_{\text{CNF}}$ as a function of inverse average temperature $1/T_{av}$ for the same four devices (the same symbols assigned) as in figure 2(b).